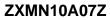




A Product Line of Diodes Incorporated



100V N-CHANNEL ENHANCEMENT MODE MOSFET IN SOT89 PACKAGE

Product Summary

V _(BR) dss	R _{DS(on)} Max	I _D max T _A = 25°C (Note 6)
100V	700mΩ @ V _{GS} = 10V	1.4A
1000	900mΩ @ V _{GS} = 6V	1.2A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance $(R_{DS(on)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Power Management functions
- Motor control
- Disconnect switches

Features and Benefits

- Low On-Resistance
- Low Threshold
- Fast Switching Speed
- Low Gate Drive
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

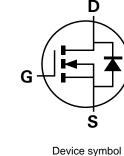
Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish
- Weight: 0.052 grams (approximate)

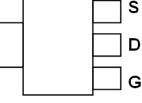
D



Top View







Top View Pin-Out

Ordering Information (Note 4)

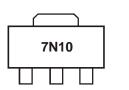
Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN10A07ZTA	7N10	7	12	1,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

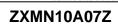
4. For packaging details, go to our website at http://www.diodes.com

Marking Information



7N10 = Product type Marking Code





7F

15X

Maximum Ratings $@T_A = 25^{\circ}C$ unless otherwise specified

Characteristic Drain-Source Voltage			Symbol	Value 100	Unit V
			V _{DSS}		
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current	Steady State	(a) $V_{GS} = 10V; T_A = 25^{\circ}C$ (Note 6) (b) $V_{GS} = 10V; T_A = 70^{\circ}C$ (Note 6) (c) $V_{GS} = 10V; T_A = 25^{\circ}C$ (Note 5)	ID	1.4 1.1 1.0	A
Pulsed Drain Current (Note 7)	-		IDM	4.2	A
Continuous Source Current (Body Diode) (Note 6)		I _S	2.1	A	
Pulsed Source Current (Body Diode) (Note 7)		I _{SM}	4.2	A	

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	r Dissipation (Note 5)		W
Linear Derating Factor	PD	12	mW/°C
Power Dissipation (Note 6)	D -	2.6	W
Linear Derating Factor	PD	21	mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	83.3	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	47.4	°C/W
Thermal Resistance, Junction to Leads (Note 8)	R _{0JL}	6.36	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

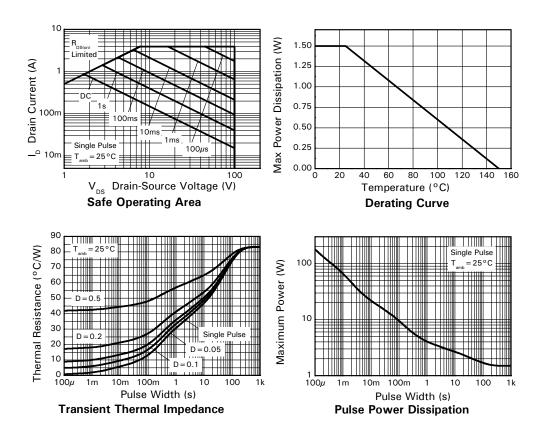
6. For a device surface mounted on FR4 PCB measured at t \leq 10 sec.

7. Repetitive rating - 25mm x 25mm FR4 PCB, D = 0.02, pulse width 300µs – pulse width limited by maximum junction temperature.

8. Thermal resistance from junction to solder-point (at the end of the drain lead).

Thermal Characteristics

Notes:





ZXMN10A07Z

ZEI

TEX

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS			71				
Drain-Source Breakdown Voltage	BV _{DSS}	100	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	1.0	μA	$V_{DS} = 100V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	-	-	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(th)}	2	-	4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance (Note 9)	P	-	-	700	mΩ	$V_{GS} = 10V, I_D = 1.5A$	
Static Drain-Source On-Resistance (Note 9)	R _{DS (ON)}	-	-	900	111.5.2	$V_{GS} = 6V, I_D = 1A$	
Forward Transconductance (Note 9 & 11)	g fs	-	1.6	-	S	V _{DS} = 15V, I _D = 1A	
Diodes Forward Voltage (Note 9)	V _{SD}	-	0.85	0.95	V	$T_J = 25^{\circ}C, I_S = 1.5A, V_{GS} = 0$	
DYNAMIC CHARACTERISTICS	·						
Input Capacitance (Note 10 & 11)	Ciss	-	138	-	pF		
Output Capacitance (Note 10 & 11)	Coss	-	12	-	pF	V _{DS} = 50V, V _{GS} = 0V, f = 1.0MHz	
Reverse Transfer Capacitance (Note 10 & 11)	Crss	-	6	-	pF	1 = 1.000112	
Gate Resistance (Note 10 & 11)	R _g	1.8	-	2.6	Ω	$f = 1MHz, V_{GS} = 0V, V_{DS} = 0V$	
Total Gate Charge (Note 10 & 11)	Qg	-	2.9	-	nC		
Gate-Source Charge (Note 10 & 11)	Q _{gs}	-	0.7	-	nC	$V_{GS} = 10V, V_{DS} = 50V,$	
Gate-Drain Charge (Note 10 & 11)	Q _{gd}	-	1	-	nC	— I _D = 1A	
Reverse Recovery Time (Note 11)	trr		27		ns	T _J = 25°C, I _F = 1A,	
Reverse Recovery Charge (Note 11)	Q _{rr}		12		nC	di/dt = 100A/µs	
Turn-On Delay Time (Note 10 & 11)	t _{D(on)}	-	1.8	-	ns		
Turn-On Rise Time (Note 10 & 11)	tr	-	1.5	-	ns	$V_{GS} = 10V, V_{DD} = 50V,$	
Turn-Off Delay Time (Note 10 & 11)	t _{D(off)}	-	4.1	-	ns	$R_{G} = 6\Omega$, $I_{D} = 1A$	
Turn-Off Fall Time (Note 10 & 11)	tf	-	2.1	-	ns	7	

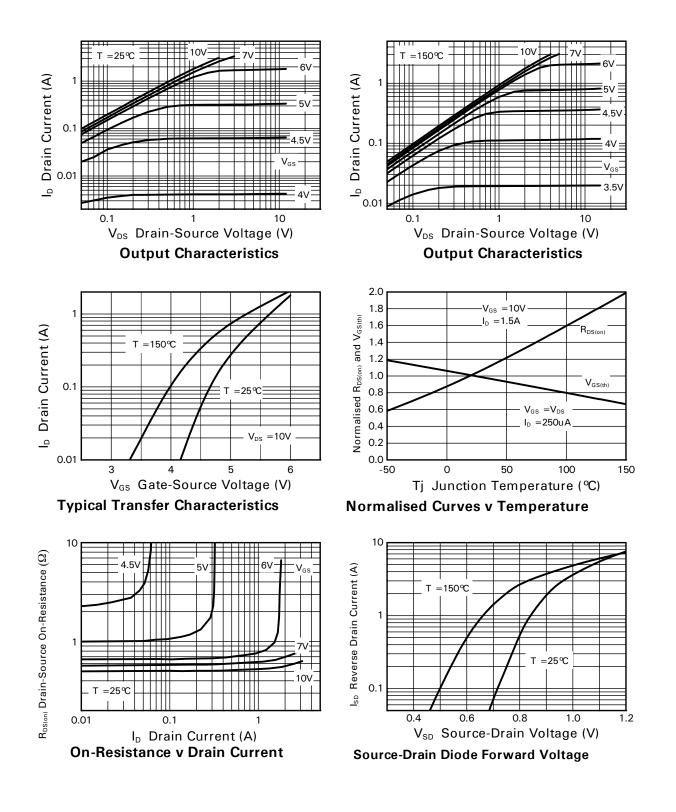
Notes:

9. Measured under pulsed conditions. Pulse width \leq 300 μs ; duty cycle \leq 2%. 10. Switching characteristics are independent of operating junction temperature. 11. For design aid only, not subject to production testing.



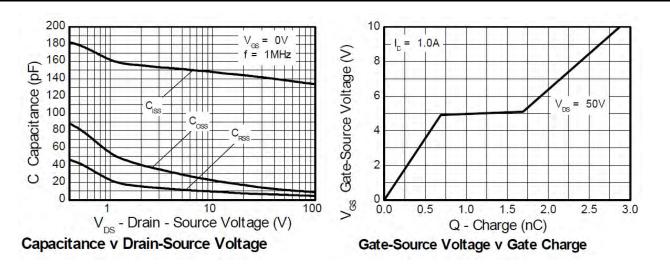


Typical Characteristics

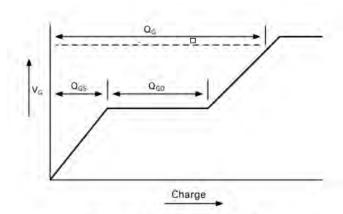




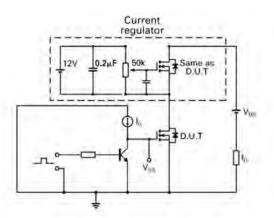
Typical Characteristics - Continued



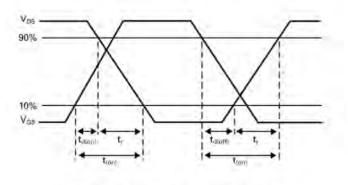
Test Circuits



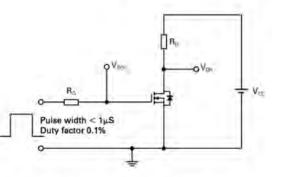
Basic gate charge waveform



Gate charge test circuit



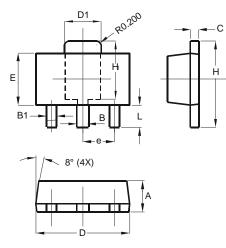
Switching time waveforms





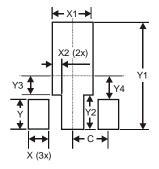


Package Outline Dimensions



SOT89				
Dim	Min	Max		
Α	1.40	1.60		
В	0.44	0.62		
B1	0.35	0.54		
С	0.35	0.44		
D	4.40	4.60		
D1	1.62	1.83		
Е	2.29	2.60		
е	1.50 Typ			
Н	3.94	4.25		
H1	2.63	2.93		
L	0.89	1.20		
All I	All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Х	0.900
X1	1.733
X2	0.416
Y	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
С	1.500



ZXMN10A07Z

IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2012, Diodes Incorporated

www.diodes.com

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Diodes Incorporated manufacturer:

Other Similar products are found below :

614233C 648584F IRFD120 JANTX2N5237 FCA20N60_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D TPCC8103,L1Q(CM MIC4420CM-TR VN1206L 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C IPP110N20N3GXK BUK954R8-60E NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE222 NTE2384 NTE2941 NTE2945 NTE2946 NTE2960 NTE2969 NTE2976 NTE6400A NTE2916 NTE2956 NTE2911 DMN2080UCB4-7 TK10A80W,S4X(S STF35N65DM2 STW70N60DM6-4 SSM6P54TU,LF SSM6P69NU,LF DMP22D4UF0-7B DMN1006UCA6-7 DMN16M9UCA6-7